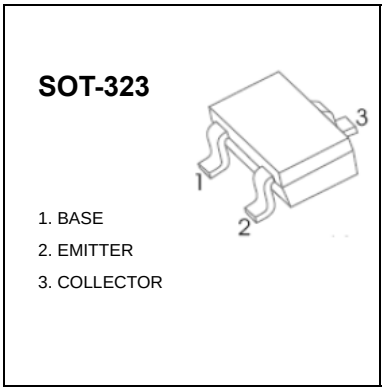
Plastic-Encapsulate Transistors

TRANSISTOR (PNP)



FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

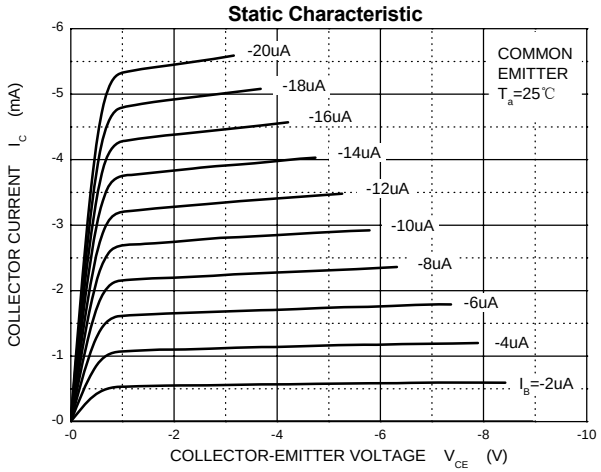
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage		V
	BC856W	-80	
	BC857W	-50	
	BC858W	-30	
V_{CEO}	Collector-Emitter Voltage		V
	BC856W	-65	
	BC857W	-45	
	BC858W	-30	
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-0.1	A
P_{C*}	Collector Power Dissipation	150	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65-150	℃

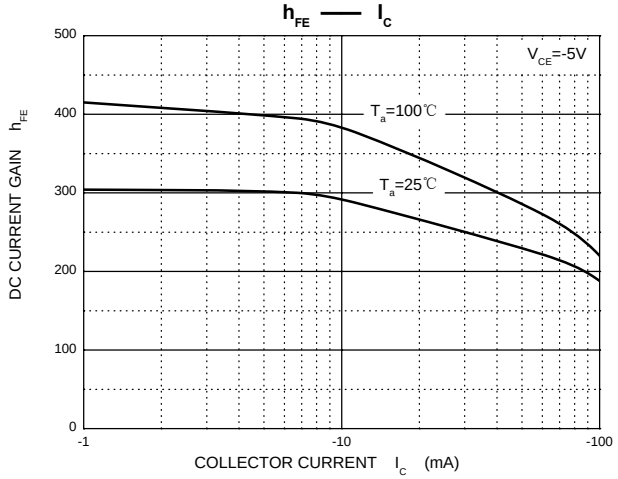
DEVICE MARKING

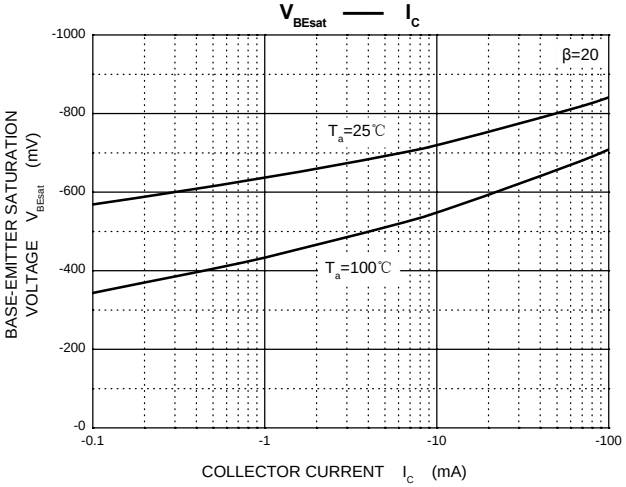
BC856AW=3A; BC856BW=3B;
BC857AW=3E; BC857BW=3F;BC857CW=3G;
BC858AW=3J; BC858BW=3K; BC858CW=3L

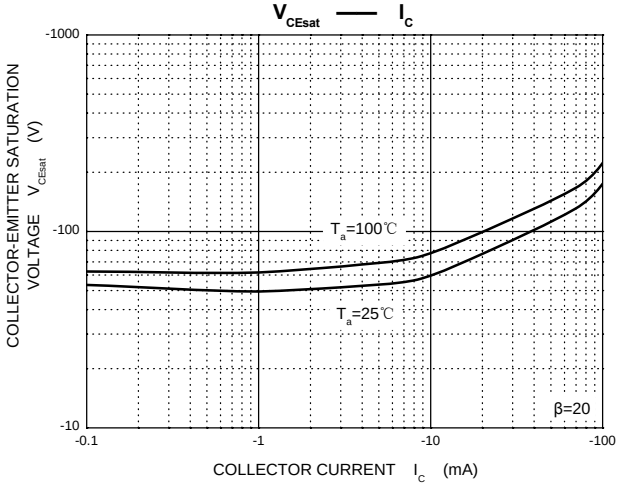
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

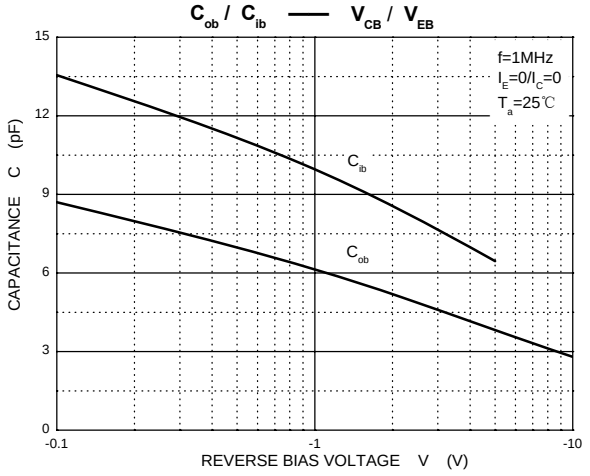
Parameter		Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	**BC856W**	V_{CBO}	I_C= -10μA, I_E=0	-80		V
	BC857W			-50		
	BC858W			-30		
Collector-emitter breakdown voltage	**BC856W**	V_{CEO}	I_C= -10mA, I_B=0	-65		V
	BC857W			-45		
	BC858W			-30		
Emitter-base breakdown voltage		V_{EBO}	I_E= -1μA, I_C=0	-5		V
Collector cut-off current		I_{CBO}	V_{CB}= -30 V , I_E=0		-15	nA
DC current gain	**BC856AW, 857AW,858AW**	h_{FE}	V_{CE}= -5V, I_C= -2mA	125	250	
	BC856BW, 857BW,858BW			220	475	
	BC857CW,BC858CW			420	800	
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C=-100mA, I_B= -5mA		-0.65	V
Base-emitter saturation voltage		$V_{BE(sat)}$	I_C= -100mA, I_B= -5mA		-1.1	V
Transition frequency		f_T	V_{CE}= -5V, I_C= -10mA f=100MHz	100		MHz
Collector capacitance		C_{ob}	V_{CB}=-10V, f=1MHz		4.5	pF

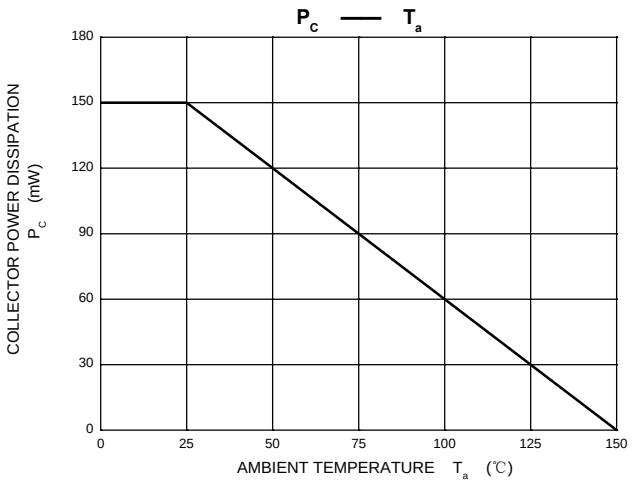






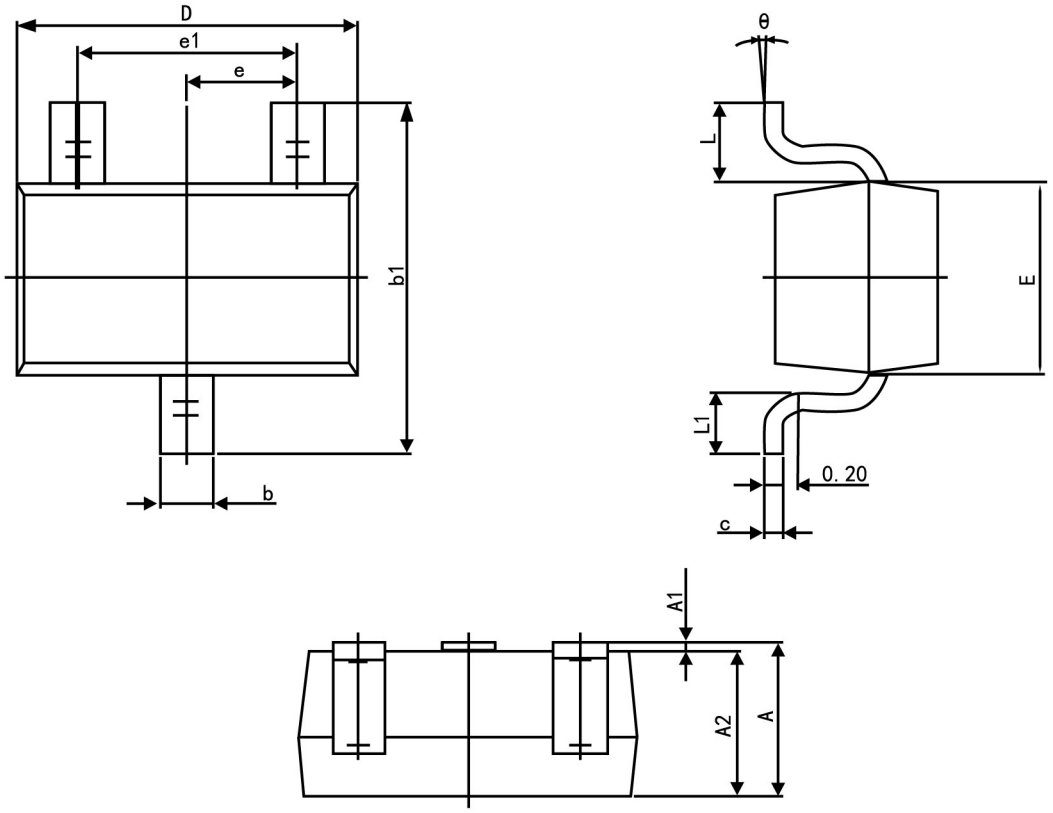






PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-323**



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.200	0.400
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
θ	**0°**	8°